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INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)		APPLICANT(S) Simon DELEONIBUS	
Sheet 1 of 1		FILING DATE September 6, 2006	

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EXAMINER	/W. Wendy Kuo/	DATE CONSIDERED 10/24/2007

Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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